





~~wherein said means for introducing said Noble gas and said means for introducing a reactive gas cooperate, during etching, to replace a flow rate of said HBr with a flow rate of said Noble gas by an amount up to and including 80%.~~

10. (Original) The plasma processing system as recited in claim 9 further comprising means for applying a magnetic field to said process space, wherein said magnetic field comprises a magnetic field strength ranging from 5 to 500 Gauss.

11. (Original) The plasma processing system as recited in claim 9, wherein said fluorine-containing gas comprises at least one of  $\text{NF}_3$ ,  $\text{SiF}_4$ , and  $\text{SF}_6$ .

12. (Original) The plasma processing system as recited in claim 9, wherein said first RF frequency is 40 MHz and said second RF frequency is 3.2 MHz.

13. (Original) The plasma processing system as recited in claim 1, wherein said reactive process gas comprises HBr,  $\text{O}_2$ , and  $\text{NF}_3$ .

14. (Original) The plasma processing system as recited in claim 13, wherein a flow rate of said HBr is about ten times greater than a flow rate of said  $\text{NF}_3$ , and said flow rate of said HBr is about fifteen times greater than a flow rate of said  $\text{O}_2$ .

15. (Canceled)

16. (Canceled)